

V_{DSS}	250V
$R_{DS(on)}$ (Max.)	105m Ω
I_D	33A
P_D	40W

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating ; RoHS compliant
- 6) 100% Avalanche tested

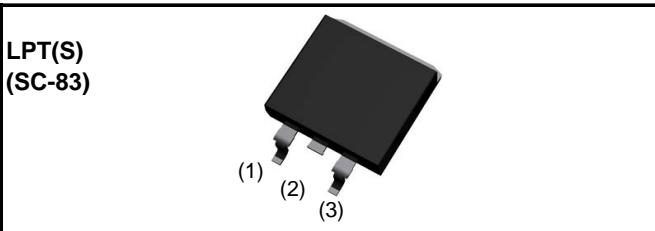
●Application

Switching Power Supply

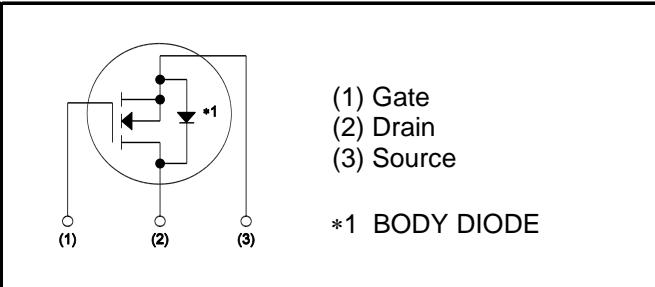
Automotive Motor Drive

Automotive Solenoid Drive

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	330
	Tape width (mm)	24
	Basic ordering unit (pcs)	1,000
	Taping code	TL
	Marking	RCJ330N25

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	250	V
Continuous drain current	I_D * ¹	± 33	A
	I_D * ¹	± 17.9	A
Pulsed drain current	$I_{D,pulse}$ * ²	± 132	A
Gate - Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse	E_{AS} * ³	74.8	mJ
Avalanche current	I_{AS} * ³	16.5	A
Power dissipation	P_D	40	W
	P_D	1.56	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R _{thJC}	-	-	3.12	°C/W
Thermal resistance, junction - ambient ^{*4}	R _{thJA}	-	-	80	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 1mA	250	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 250V, V _{GS} = 0V T _j = 25°C	-	0.1	1	μA
Gate - Source leakage current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	3.0	-	5.0	V
Static drain - source on - state resistance	R _{DS(on)} ^{*5}	V _{GS} = 10V, I _D = 16.5A	-	77	105	mΩ
		V _{GS} = 10V, I _D = 16.5A T _j = 125°C	-	165	230	
Forward transfer admittance	g _{fs}	V _{DS} = 10V, I _D = 16.5A	10	20	-	S

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$	-	4500	-	pF
Output capacitance	C_{oss}		-	220	-	
Reverse transfer capacitance	C_{rss}		-	130	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 125\text{V}, V_{GS} = 10\text{V}$ $I_D = 16.5\text{A}$ $R_L = 7.6\Omega$ $R_G = 10\Omega$	-	50	-	ns
Rise time	t_r^{*5}		-	200	-	
Turn - off delay time	$t_{d(off)}^{*5}$		-	120	-	
Fall time	t_f^{*5}		-	140	-	

● Gate Charge characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 125\text{V}$ $I_D = 33\text{A}$ $V_{GS} = 10\text{V}$	-	80	-	nC
Gate - Source charge	Q_{gs}^{*5}		-	25	-	
Gate - Drain charge	Q_{gd}^{*5}		-	27	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 125\text{V}, I_D = 33\text{A}$	-	6.6	-	V

● Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	26	A
Pulsed source current	I_{SM}^{*2}		-	-	104	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = 33\text{A}$ $I_S = 16.5\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*5}		-	145	-	ns
Reverse recovery charge	Q_{rr}^{*5}		-	670	-	nC

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 $L \approx 500\mu\text{H}$, $V_{DD} = 50\text{V}$, $R_g = 25\Omega$, starting $T_j = 25^\circ\text{C}$

*4 Mounted on a epoxy PCB FR4 (20mm × 30mm × 0.8mm)

*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

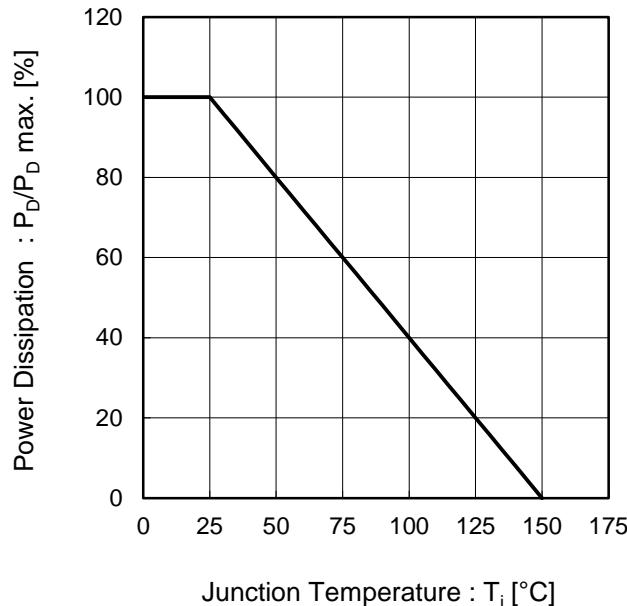


Fig.2 Maximum Safe Operating Area

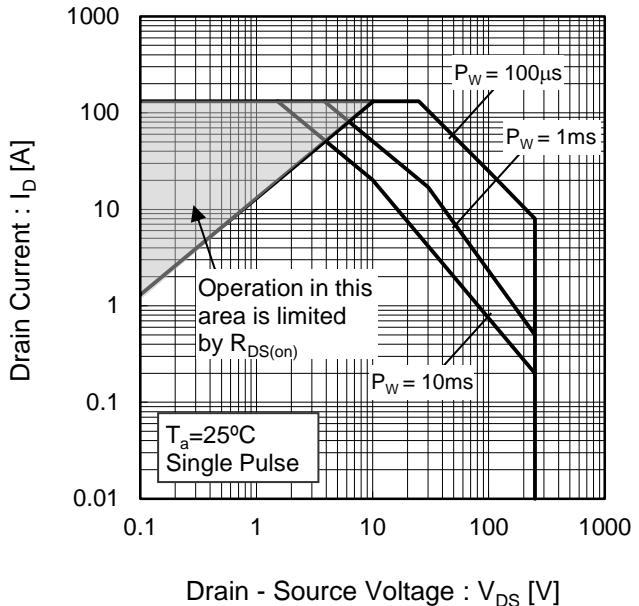
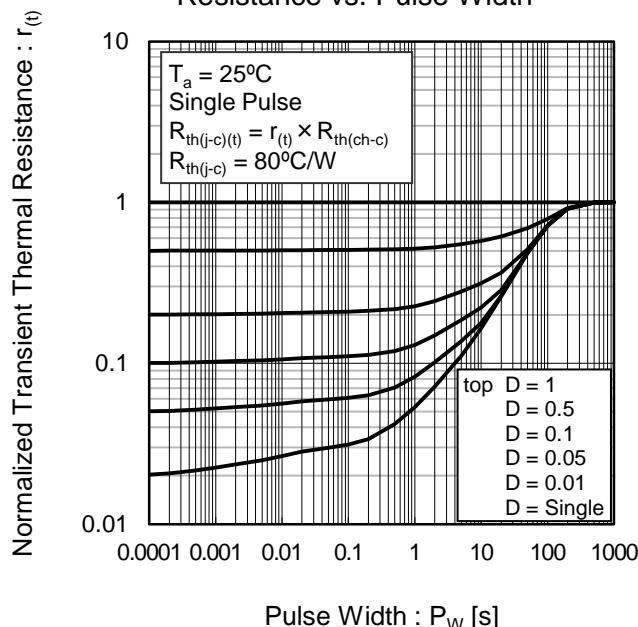


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



● Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

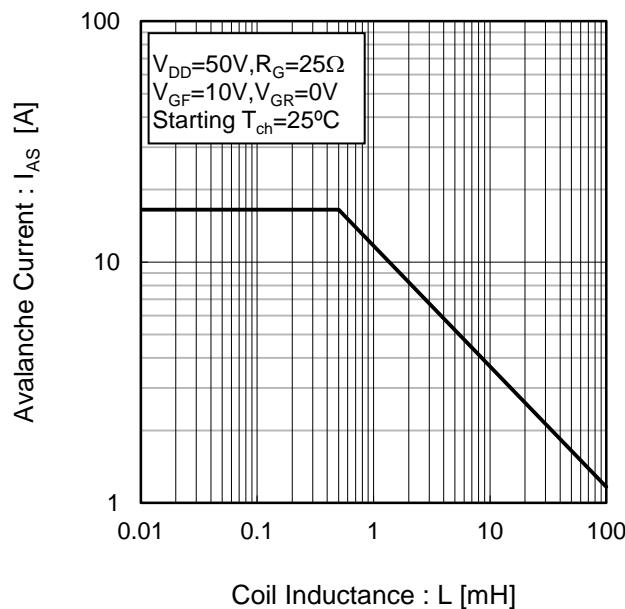


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

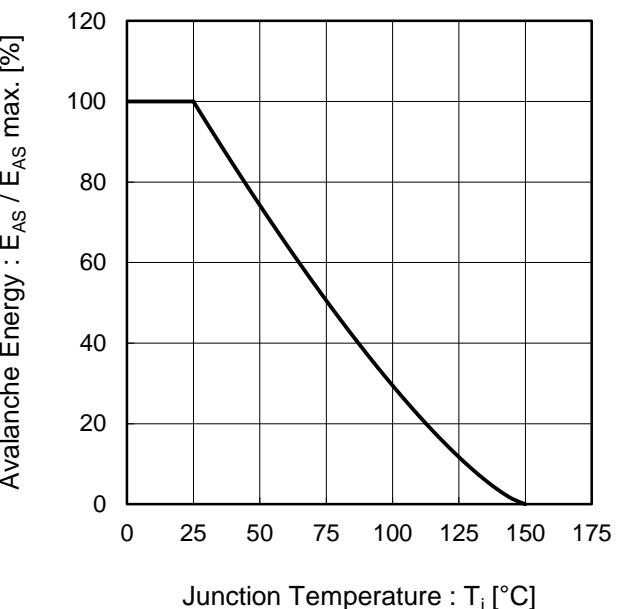


Fig.6 Typical Output Characteristics(I)

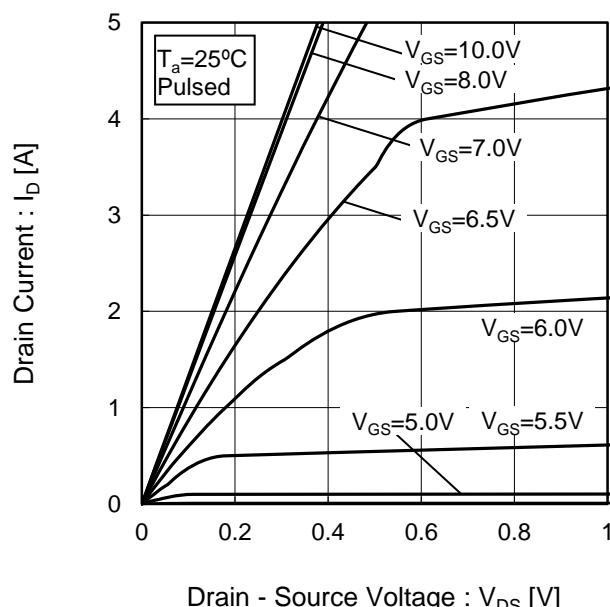
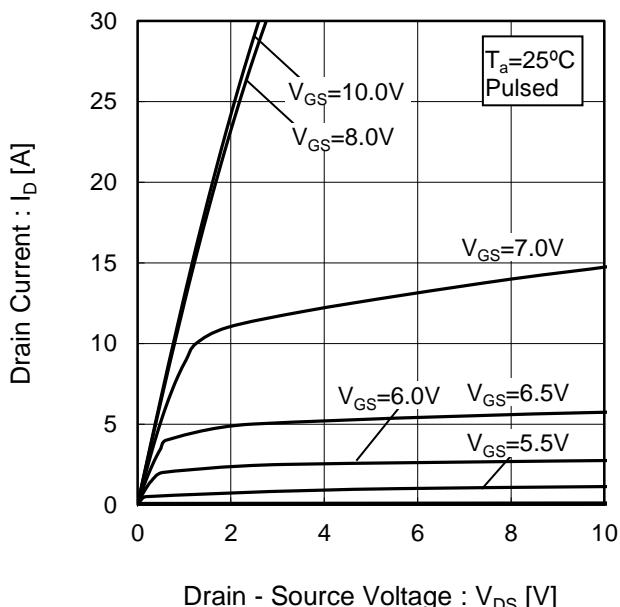


Fig.7 Typical Output Characteristics(II)



●Electrical characteristic curves

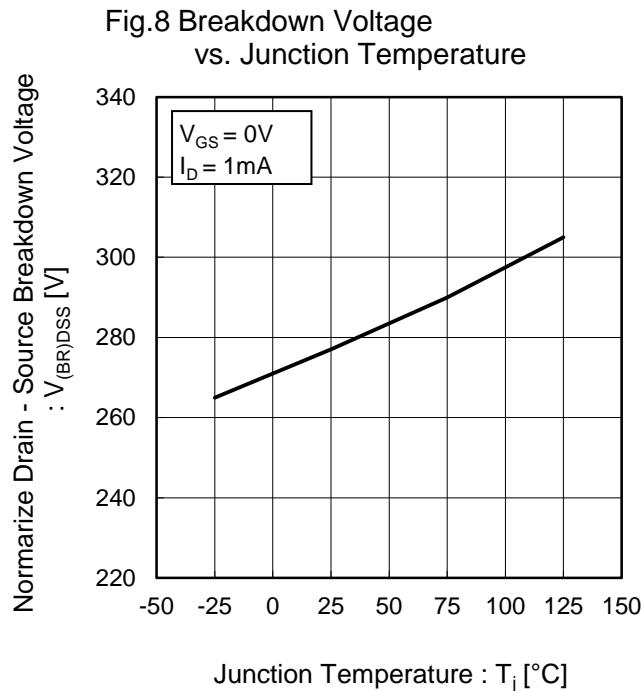


Fig.9 Typical Transfer Characteristics

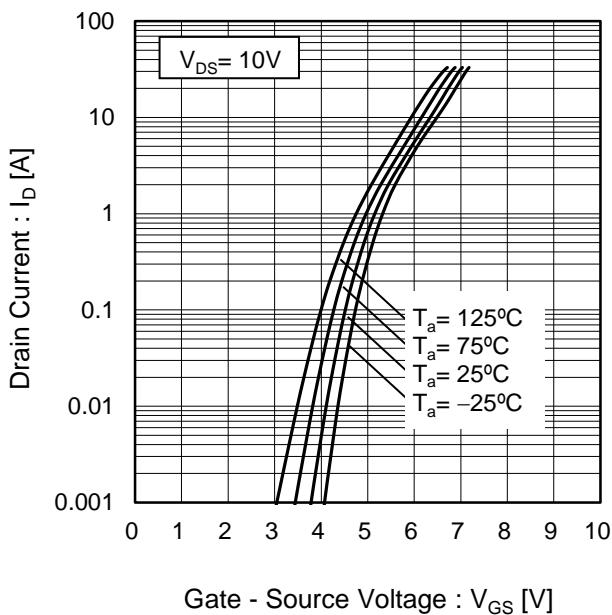


Fig.10 Gate Threshold Voltage vs. Junction Temperature

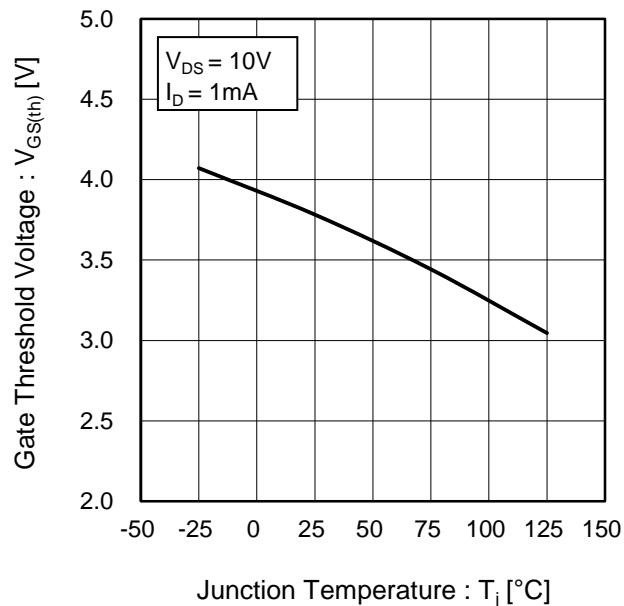
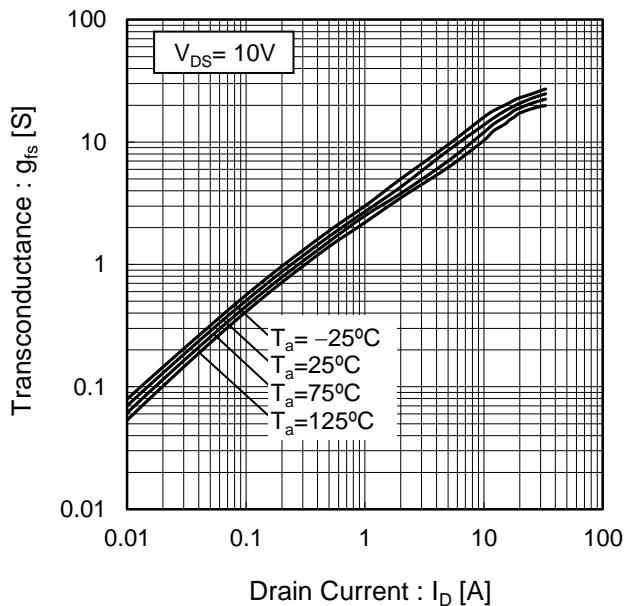


Fig.11 Transconductance vs. Drain Current



● Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

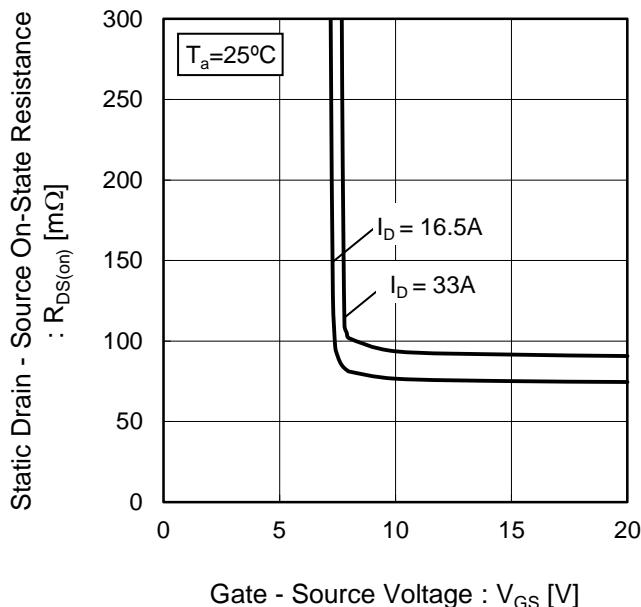


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I_D)

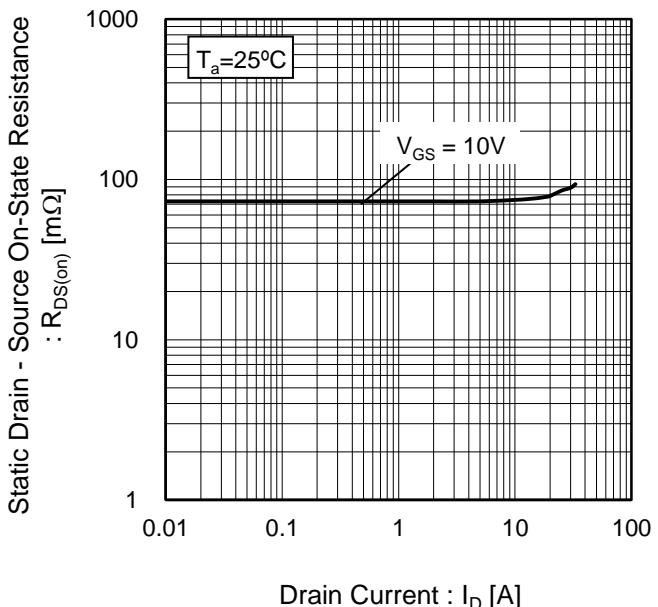
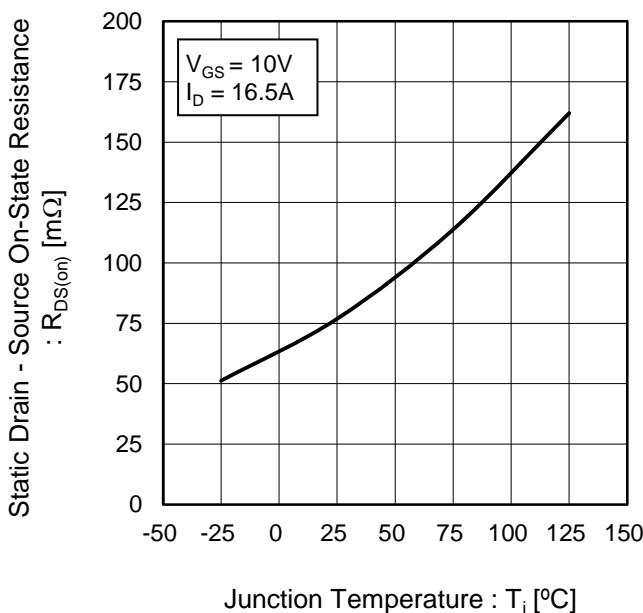


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



● Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I_D)

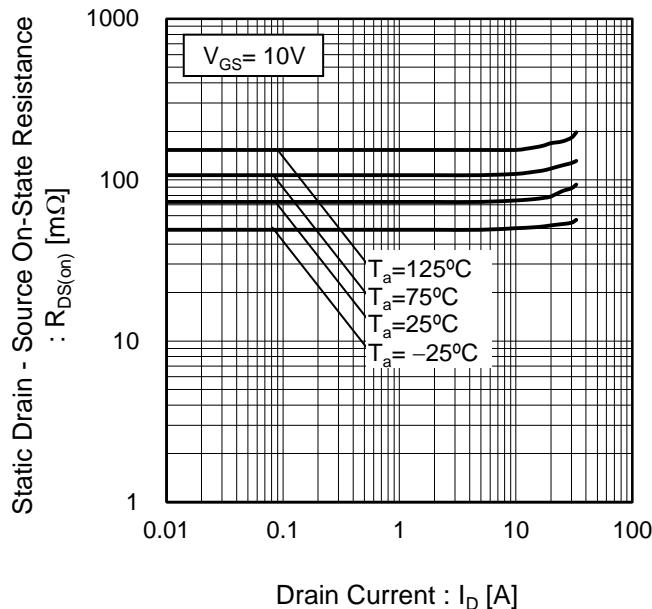
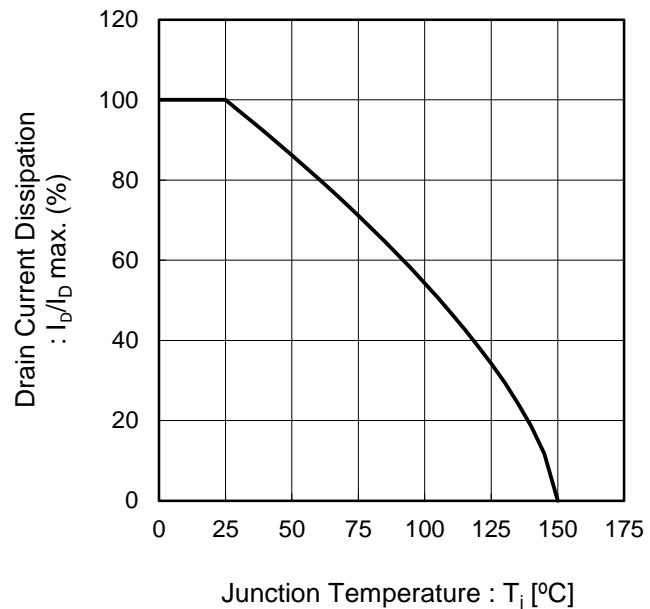


Fig.16 Drain Current Derating Curve



● Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

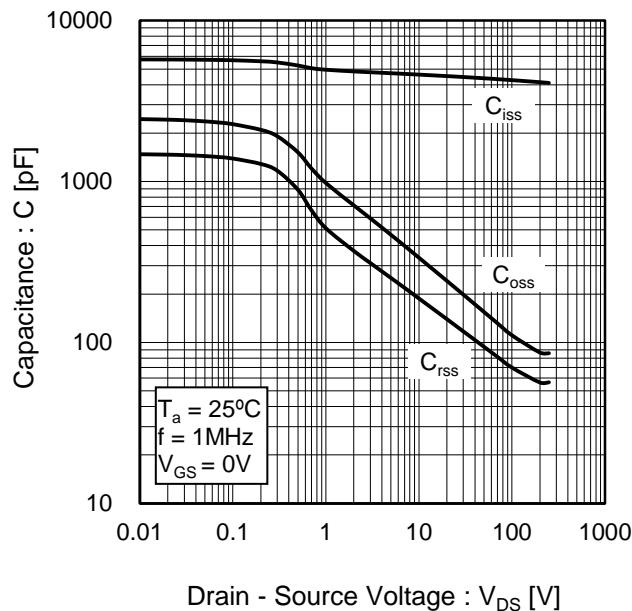


Fig.18 Switching Characteristics

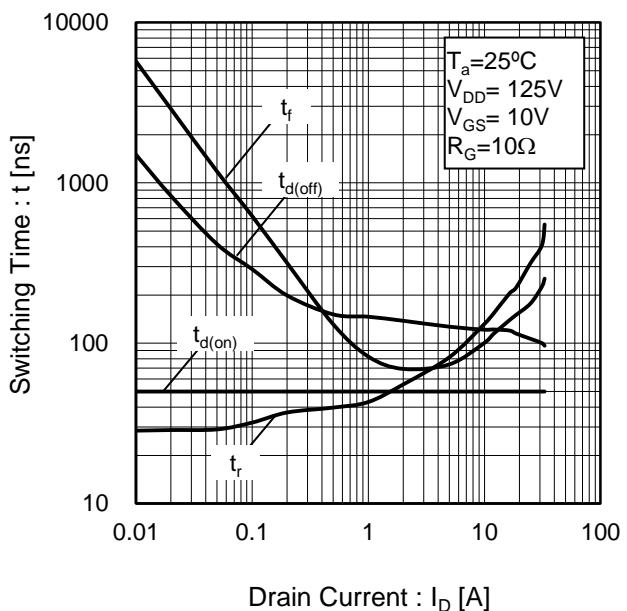
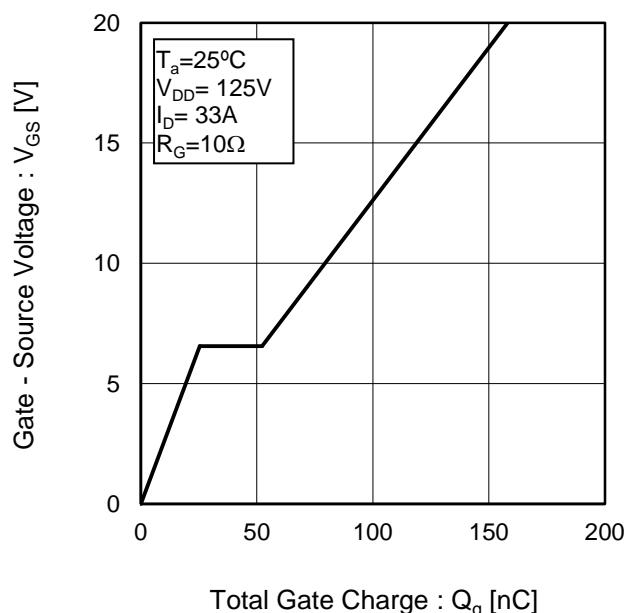


Fig.19 Dynamic Input Characteristics



● Electrical characteristic curves

Fig.20 Source Current
vs. Source - Drain Voltage

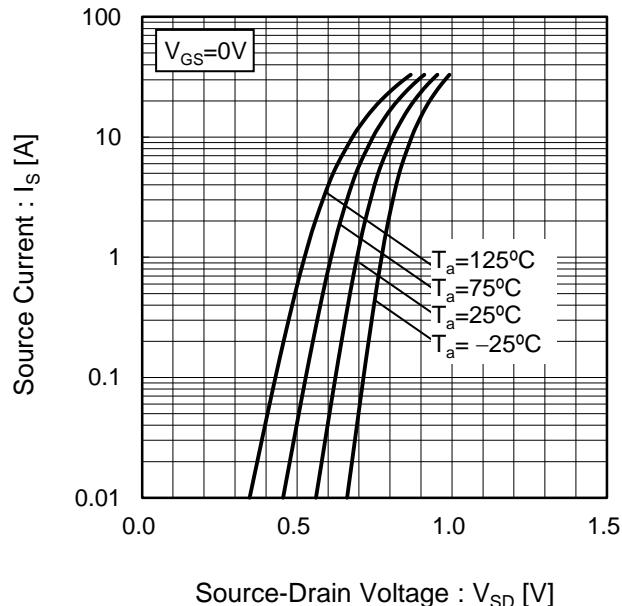
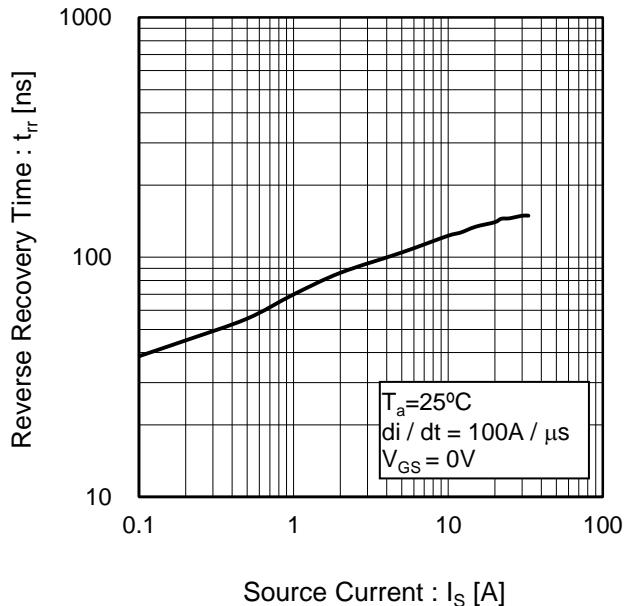


Fig21 Reverse Recovery Time
vs. Source Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

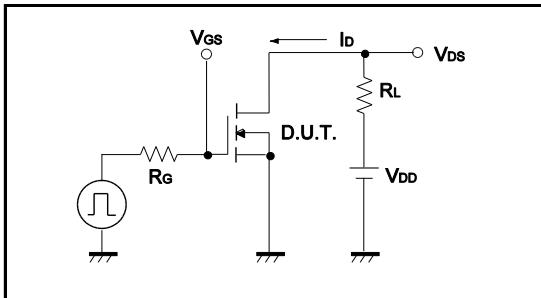


Fig.1-2 Switching Waveforms

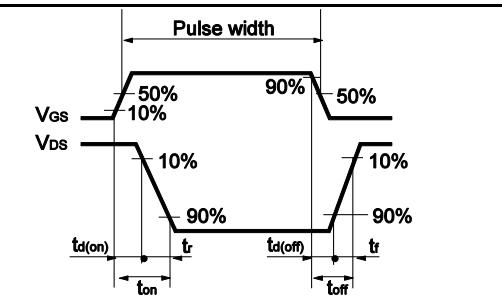


Fig.2-1 Gate Charge Measurement Circuit

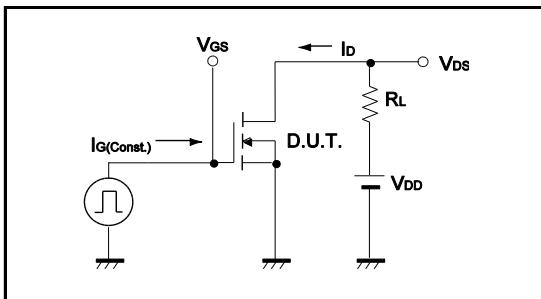


Fig.2-2 Gate Charge Waveform

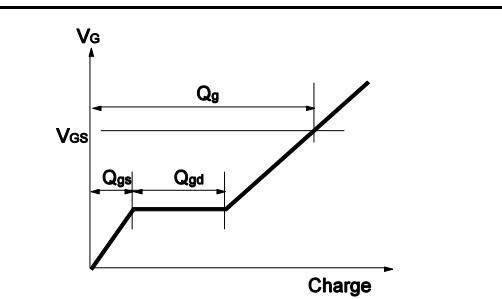


Fig.3-1 Avalanche Measurement Circuit

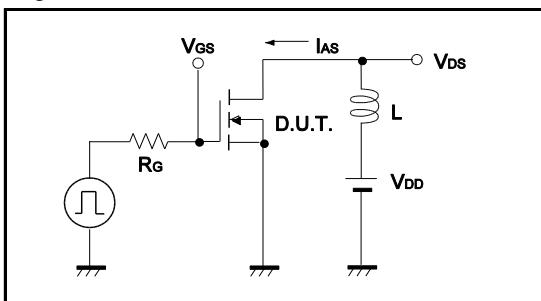
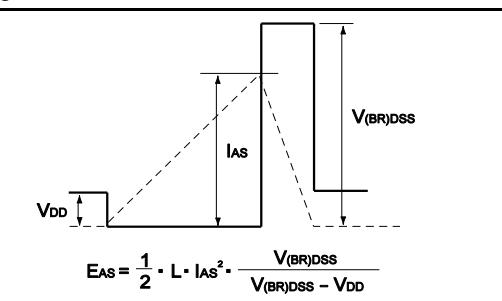
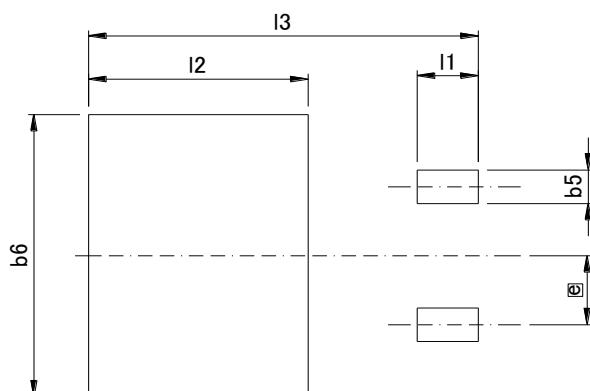
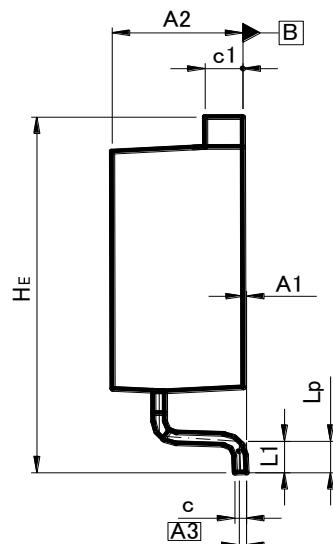
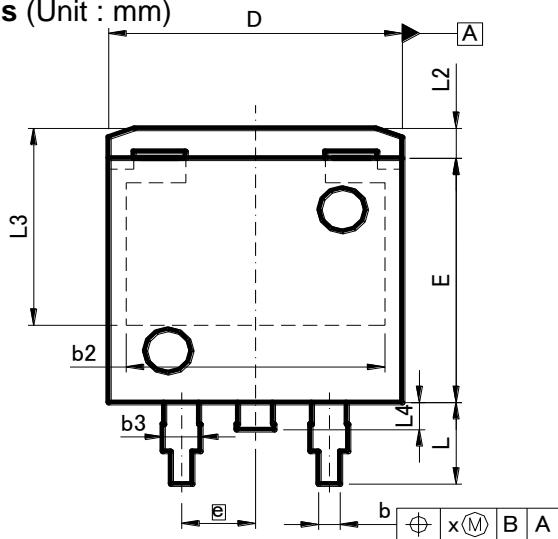


Fig.3-2 Avalanche Waveform



● Dimensions (Unit : mm)

LPTS



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.30	0.000	0.012
A2	4.30	4.70	0.169	0.185
A3	0.25		0.010	
b	0.68	0.98	0.027	0.039
b2	8.90		0.350	
b3	1.14	1.44	0.045	0.057
c	0.30	0.60	0.012	0.024
c1	1.10	1.50	0.043	0.059
D	9.80	10.40	0.386	0.409
E	8.80	9.20	0.346	0.362
e	2.54		0.100	
HE	12.80	13.40	0.504	0.528
L	2.70	3.30	0.106	0.130
L1	0.90	1.50	0.035	0.059
L2	1.10		0.043	
L3	7.25		0.285	
L4	1.00		0.039	
Lp	0.90	1.50	0.035	0.059
x	-	0.25	-	0.010

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	-	1.23	-	0.049
b6	-	10.40	-	0.409
I1	-	2.10	-	0.083
I2	-	7.55	-	0.297
I3	-	13.40	-	0.528

Dimension in mm / inches

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